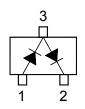
## HIGH-SPEED DOUBLE SWITCHING DIODE





SOT-323 Plastic Package

Marking Code: A7

## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V <sub>RRM</sub>	85	V
Continuous Reverse Voltage		V <sub>R</sub>	75	V
Continuous Forward Current				
	Single Diode Load 1)	I <sub>F</sub>	150	mA
	Double Diode Load <sup>1)</sup>		130	
Repetitive Peak Forward Current		I <sub>FRM</sub>	500	mA
Non-repetitive Peak Forward Current				
Square Wave; T <sub>j</sub> = 25 °C Prior to Surge	at t = 1 µs	I <sub>FSM</sub>	4	A
	at t = 1 ms		1	
	at t = 1 s		0.5	
Total Power Dissipation		P <sub>tot</sub>	200	mW
Junction Temperature		Tj	150	°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance from Junction to Ambient <sup>1)</sup>		$R_{thj-a}$	625	K/W

<sup>1)</sup> Device mounted on an FR4 printed-circuit board.

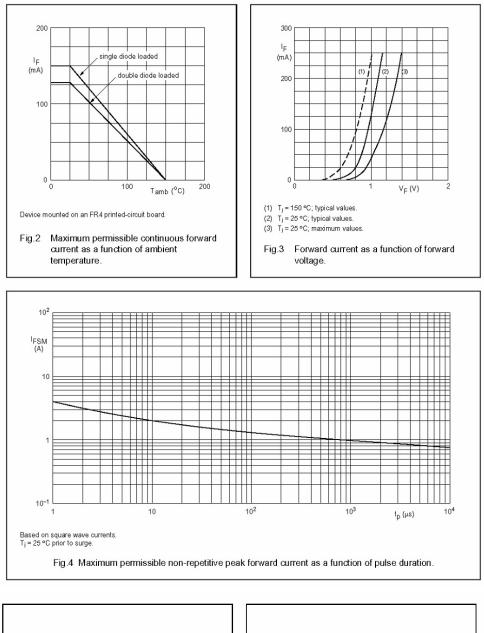
## Characteristics at T<sub>j</sub> = 25°C

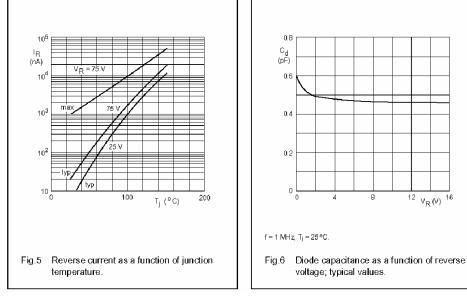
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V <sub>F</sub>	0.715 0.855 1 1.25	V
Reverse Current   at $V_R = 25 V$ at $V_R = 75 V$ at $V_R = 25 V$ , $T_j = 150 °C$ at $V_R = 75 V$ , $T_j = 150 °C$	I <sub>R</sub>	30 1 30 50	nA μA μA μA
Diode Capacitance at f = 1 MHz; V <sub>R</sub> = 0	C <sub>d</sub>	1.5	pF
Reverse Recovery Time at $I_F$ = 10 mA to $I_R$ = 10 mA, $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA	t <sub>rr</sub>	4	ns
Forward Recovery Voltage at I <sub>F</sub> = 10mA, t <sub>r</sub> = 20 ns	V <sub>fr</sub>	1.75	V













## SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company

listed on the Hong Kong Stock Exchange, Stock Code: 724)



<sup>12</sup> V<sub>R</sub>(V) <sup>16</sup>

Dated : 12/01/2006